

A Low Power TPC Readout ASIC in 65nm CMOS

Wei Liu^{1,2}, Canwen Liu^{1,2}, **Zhi Deng**^{1,2}, Fule Li³, Yulan Li^{1,2}, Huirong Qi⁴

¹ Department of Engineering Physics, Tsinghua University, Beijing, China

² Key Laboratory of Particle & Radiation Imaging, Ministry of Education, Beijing, China

³ Institute of Microelectronics, Tsinghua University, Beijing, China

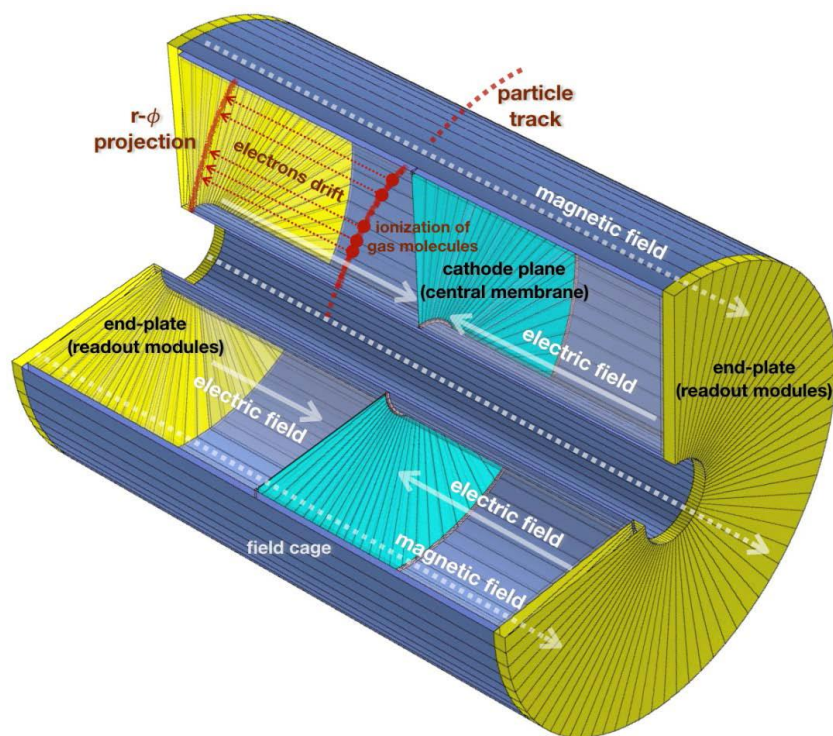
⁴ Institute of High Energy Physics, Chinese Academy of Science, Beijing, China



Outline

- Introduction
- Chip Architecture and Specifications
- Circuit Design
- Test Results
- Summary

Introduction



Momentum resolution (B=3.5T)	$\delta(1/p_t \approx 10^{-4}/GeV/c)$
δ_{point} in $r\phi$	<100 μm
δ_{point} in rZ	0.4-1.4 mm
Inner radius	329 mm
Outer radius	1800 mm
Drift length	2350 mm
TPC material budget	$\approx 0.05X_0$ incl. field cage $< 0.25X_0$ for readout endcap
Pad pitch/no. padrows	$\approx 1 \text{ mm} \times (4\sim 10\text{mm}) / \approx 200$
2-hit resolution	$\approx 2 \text{ mm}$
Efficiency	$>97\%$ for TPC only ($p_t > 1GeV$) $>99\%$ all tracking ($p_t > 1GeV$)

- TPC can provide large-volume high-precision 3D track measurement with stringent material budget
- In order to achieve high spatial resolution, small pads (e.g. 1 mm x 6mm) are needed, resulting **~1 million** channel of readout electronics
- Need low power consumption readout electronics **working at continuous mode**

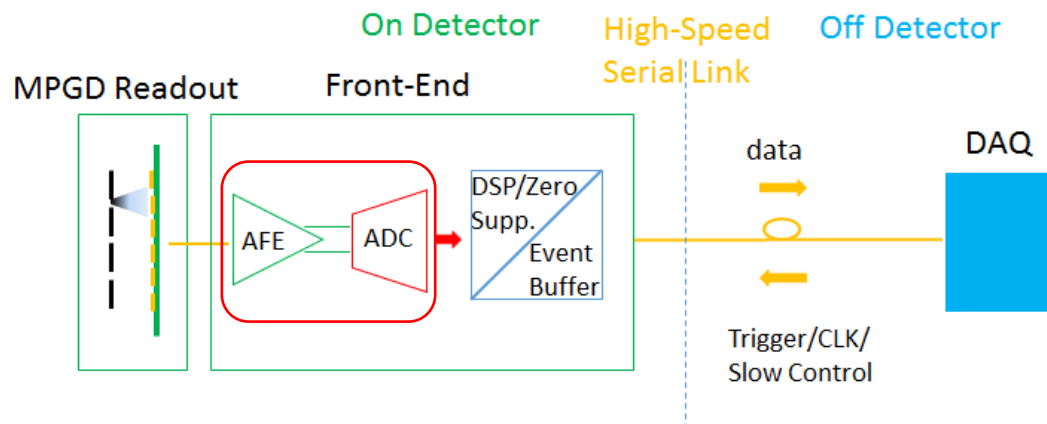
Current TPC Readout ASICs

- Waveform sampling (8-10 bit, ~10MS/s) is required for TPC signal processing
- Direct ADC sampling is more preferable than SCA for high rate applications
- Lower power consumption → less cooling → less material

	PASA/ALTRO	AGET	Super-ALTRO	SAMPA
TPC	ALICE	T2K	ILC	ALICE upgrade
Pad size	4x7.5 mm ²	6.9x9.7 mm ²	1x6 mm ²	4x7.5 mm ²
Pad channels	5.7 x 10 ⁵	1.25 x 10 ⁵	1-2 x 10 ⁶	5.7 x 10 ⁵
Readout Chamber	MWPC	MicroMegas	GEM/MicroMegas	GEM
Gain	12 mV/fC	0.2-17 mV/fC	12-27 mV/fC	20/30 mV/fC
Shaper	CR-(RC) ⁴	CR-(RC) ²	CR-(RC) ⁴	CR-(RC) ⁴
Peaking time	200 ns	50 ns-1us	30-120 ns	80/160 ns
ENC	385 e	850 e @ 200ns	520 e	482 e @ 180ns
Waveform Sampler	ADC	SCA	ADC	ADC
Sampling frequency	10 MSPS	1-100 MSPS	40 MSPS	20 MSPS
Dynamic range	10 bit	12 bit(external)	10 bit	10 bit
Power consumption	32 mW/ch	<10 mW/ch	47.3 mW/ch	8 mW/ch
CMOS Process	250 nm	350 nm	130 nm	130 nm

Chip Architecture

- In order to reduce the power consumption:
 - Using more advanced 65 nm CMOS process favoring digital logics
 - Reducing analog circuits:
 - $CR-(RC)^n \rightarrow CR-RC$, moving high order shaping to digital domain
 - ADC structure : pipeline \rightarrow SAR (Successive Approximation Register)
- So far only the AFE and the ADC parts have been implemented



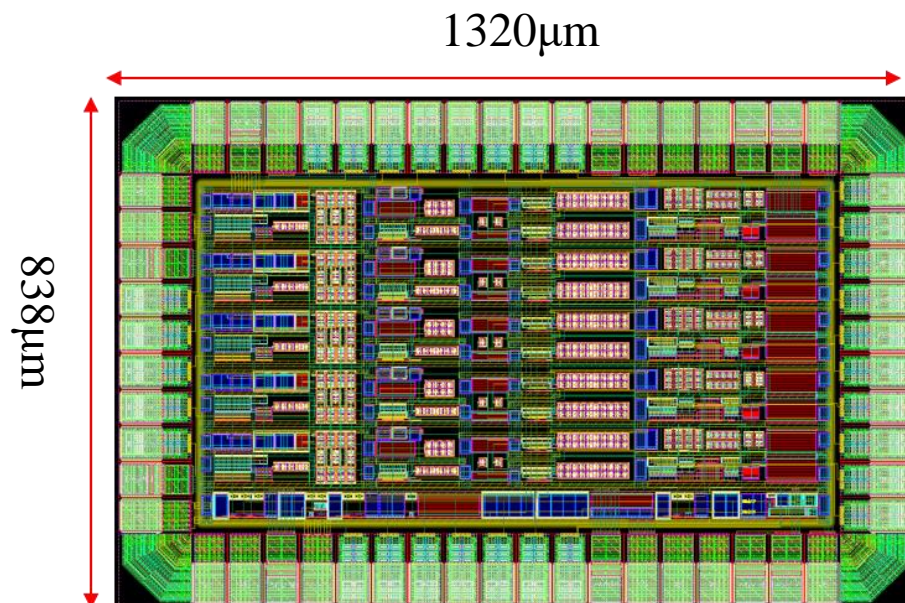
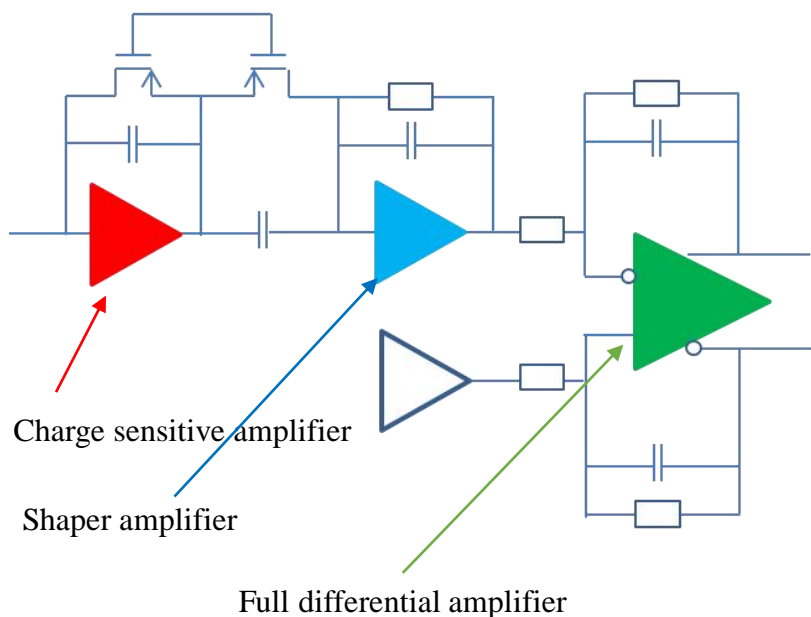
Specifications

- AFE + waveform sampling ADC + direct output
- Process: TSMC 65nm LP
- Power supply: 1.2V

AFE(Analog Front-End)		SAR-ADC	
Signal Polarity	Negative	Input Range	-0.6 V ~ 0.6 V diff.
Detector Capacitance	5-20 pF	Resolution	10 bit
Shaper	CR-RC	Sampling Rate	40 MS/s
Shaping Time	160 ns	DNL	<0.6 LSB
ENC (Equivalent Noise Charge)	<500 e @ 10pF	INL	<0.6 LSB
Dynamic Range	120 fC max.	SFDR @ 2MHz, 40MSPS	68 dBc
Gain	10-40 mV/fC	SINAD	57 dB
INL (Integrated Non-Linearity)	<1%	ENOB	>9.2 bit @ 2MHz
Crosstalk	<1%	Power Consumption (ADC)	<2.5 mW/ch
Power Consumption (AFE)	<2.5 mW/ch		

Circuit Design: Analog Front-End

- Charge sensitive preamplifier
- CR-RC shaper
- Differential output-stage



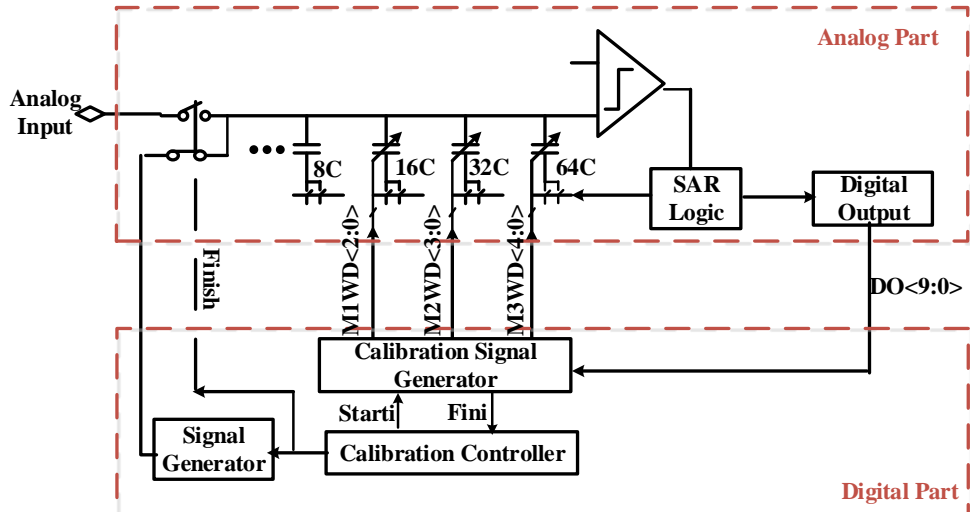
The test results of the first prototype chip in 2017/18:

- Power consumption: 2.02 mW/channel
- Gain: 9.8 mV/fC
- ENC(equivalent noise charge): 589 e @10pF

W. Liu, et. al. JINST 2020

W. Liu, et.al. JPCS 2020

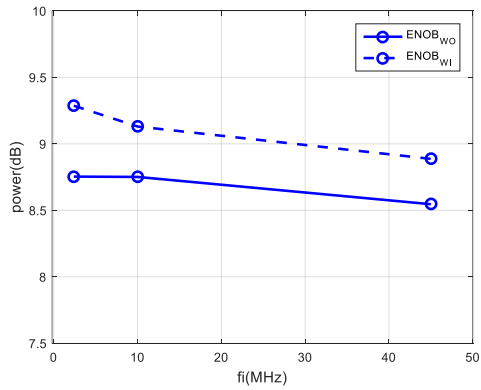
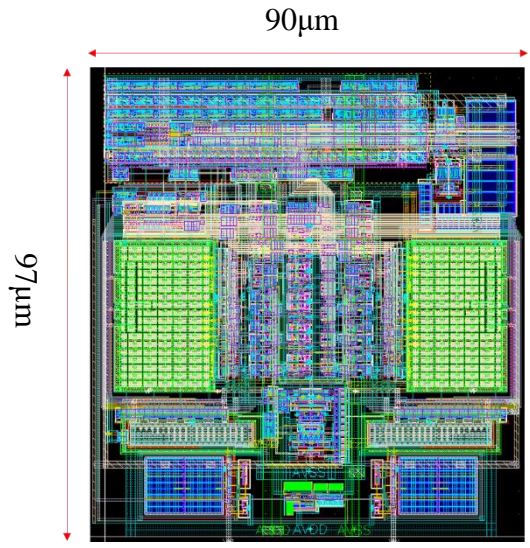
Circuit Design: SAR ADC



Module Name	Power(mW)
Chip	4.0
Referred Buffer Module	0.25
SAR ADC Core Module	1.0
Clock Generation Module , etc	2.75

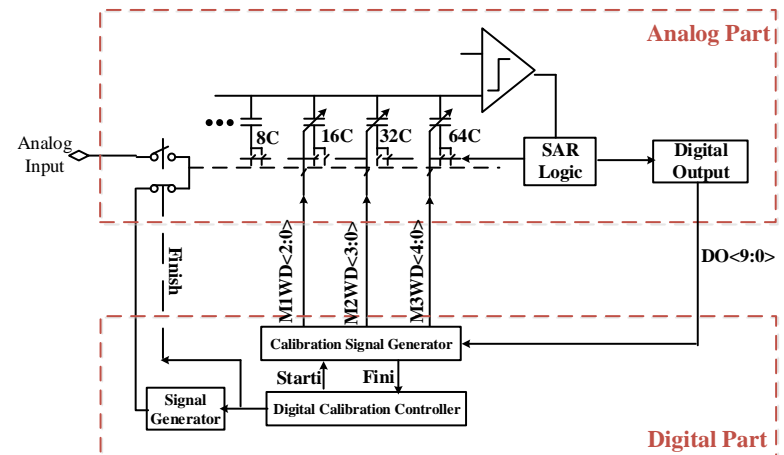
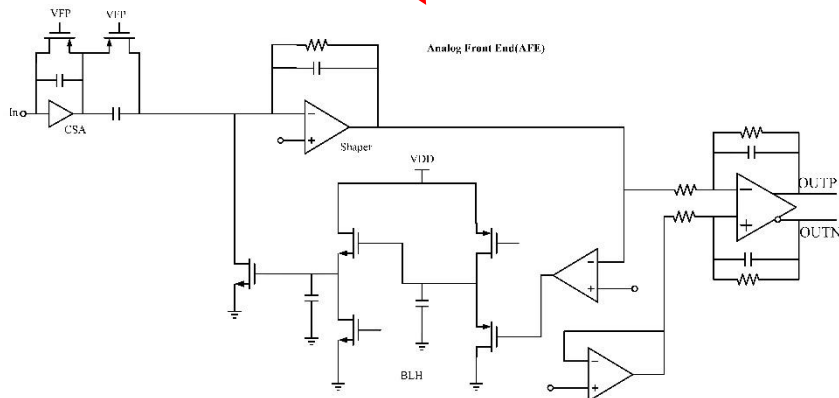
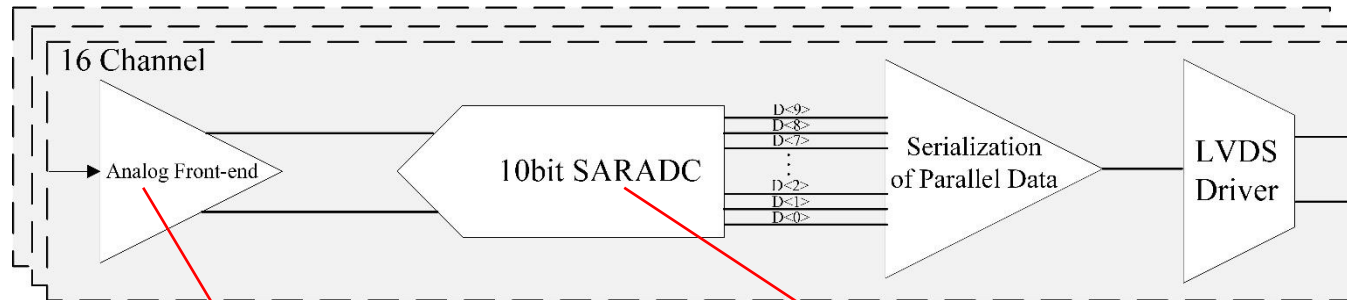
The test results of first prototype SAR ADC in 2017/18

- The core power consumption of SAR ADC:1 mW
- Maximum INL/DNL=0.6 LSB
- ENOB=9.15 bit @ 50 MS/s with 2.4 MHz sine input



W. Liu, et. al, JINST 2020
 X. Wang, et. al, IEEE TCSII.2020

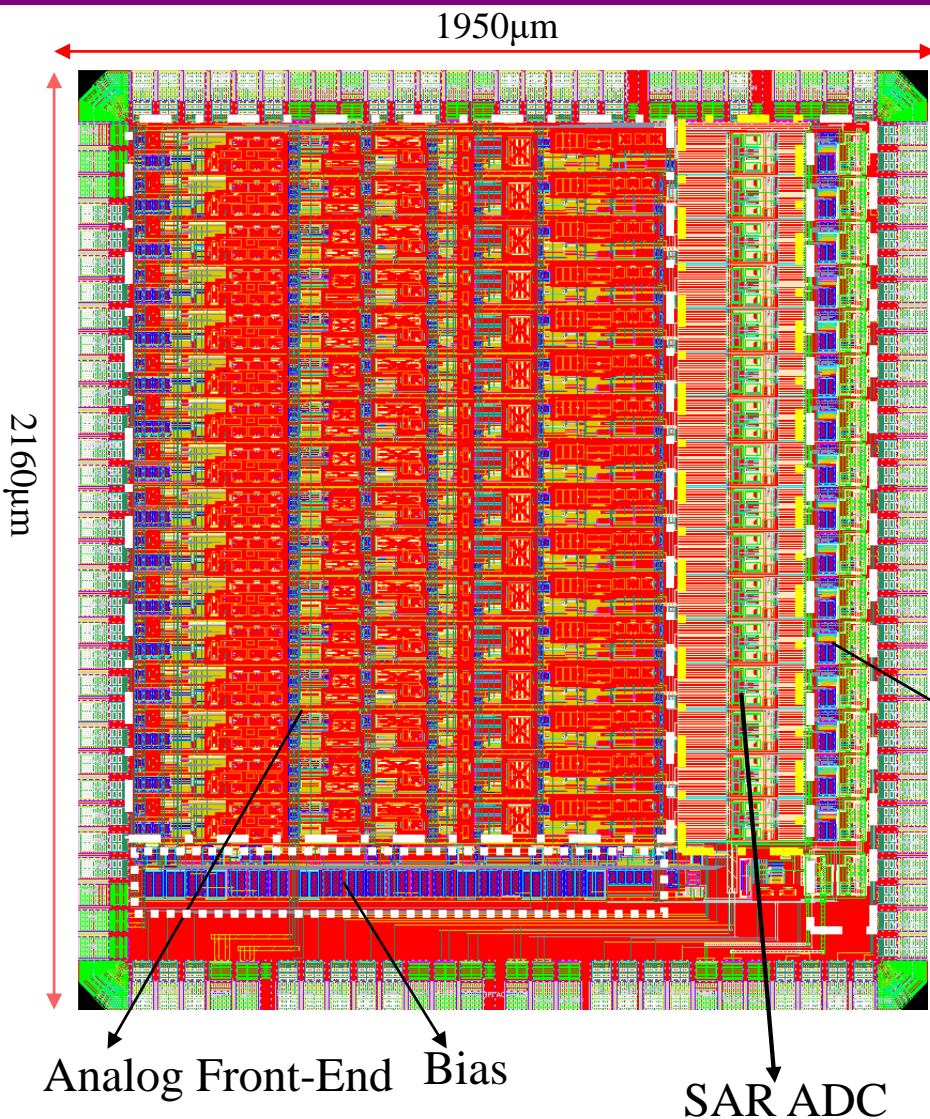
The 16-ch TPC Readout ASIC



The second prototype chip submitted in 2019:

- 16 channel AFE+ADC+LVDS data output
- The power consumption of the AFE optimized from 2.02 mW/ch to 1.4 mW/ch
- ENC optimized from 589 e to 303 e @ 10 pF

The Layout of the TPC Readout ASIC

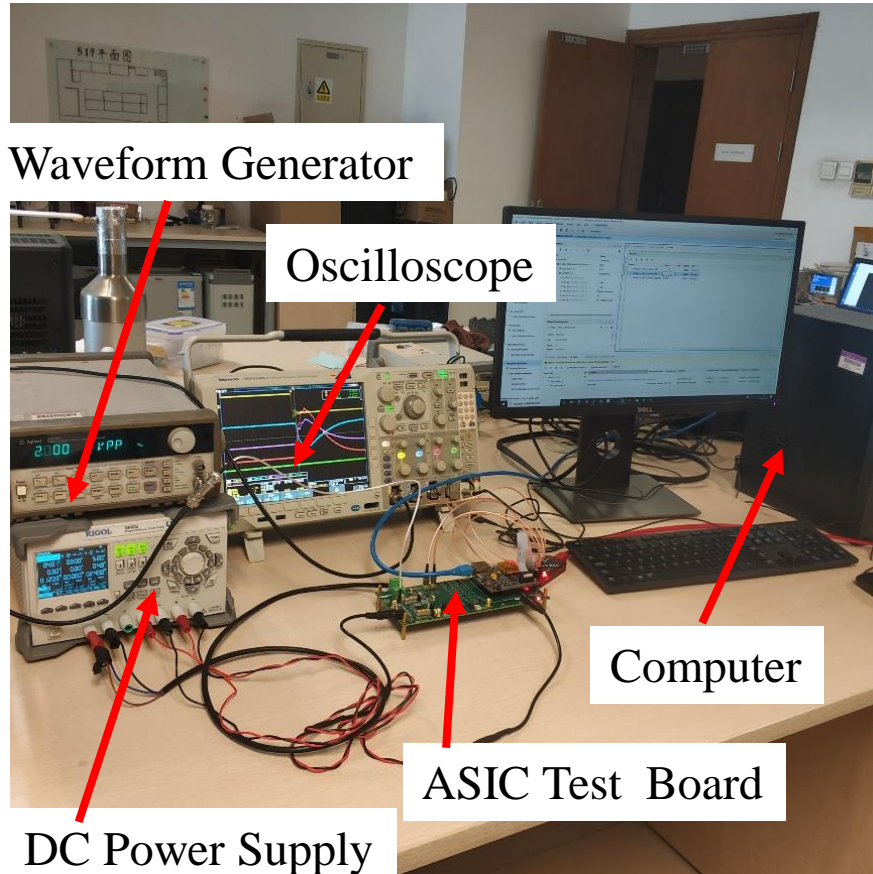


- The floor plan in layout :
 - The die size of 1950 μm x 2160 μm
 - Analog Front-End , SPI, SAR ADC, LVDS driver are supplied by separate power
- The ASIC have been taped out in November, 2019 and is being evaluated

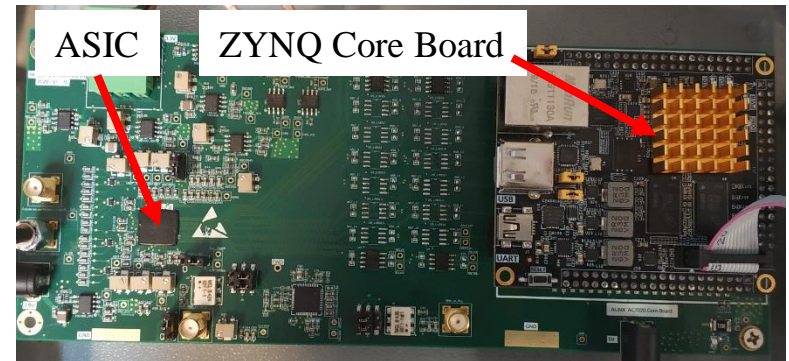
LVDS driver

Test Setup

- Test Setup

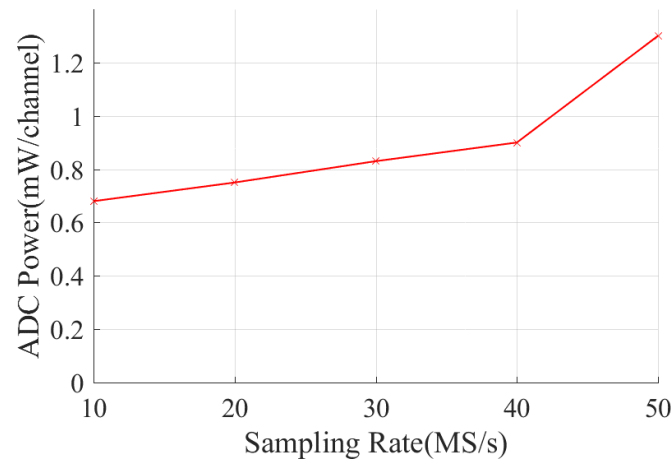


- ASIC Test Board



Power Consumption

- The power consumption of the AFE: **1.43 mW/ch** (1.40 mW/ch sim.)
- The power consumption of the ADC increases as the sampling rate



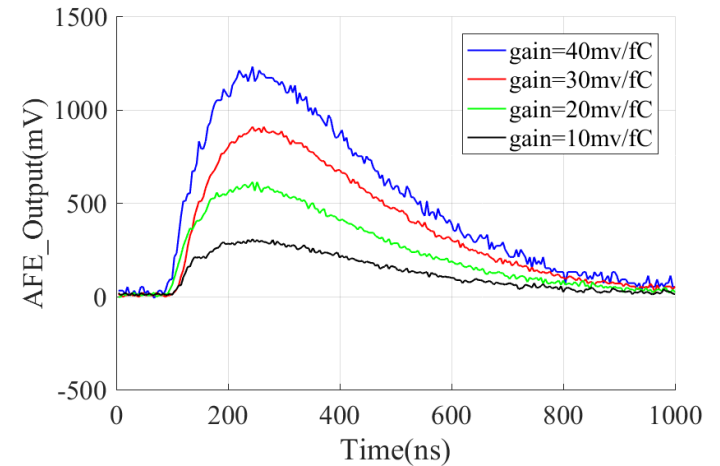
	AFE (mW/ch)	ADC (mW/ch)	Total (mW/ch)
Frist run (simulation)	1.93	1.0	2.93
First run (measured)	2.02	1.0	3.02
Second run (simulation)	1.40	1.0	2.40
Second run (measured)	1.43	0.9 @40MS/s	2.33

Transient waveforms

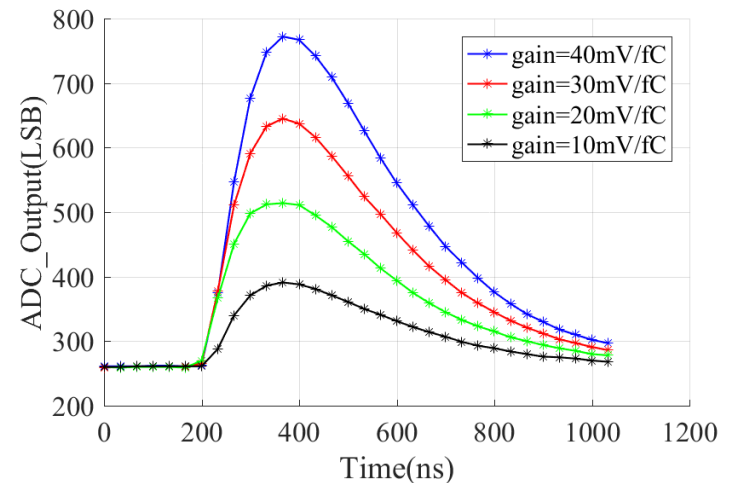
- Transient outputs
 - Differential baseline can be externally adjusted



AFE Monitor Transient outputs

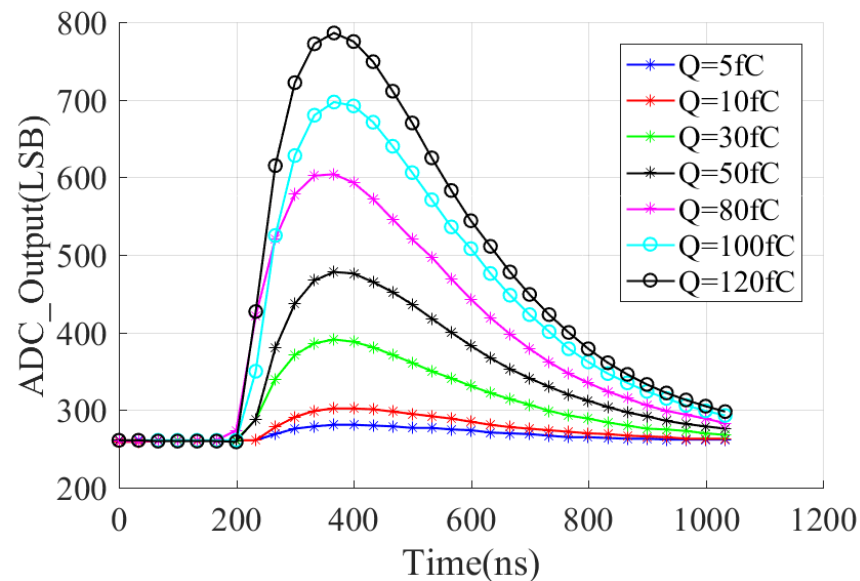


ADC Transient outputs @ 30MSPS

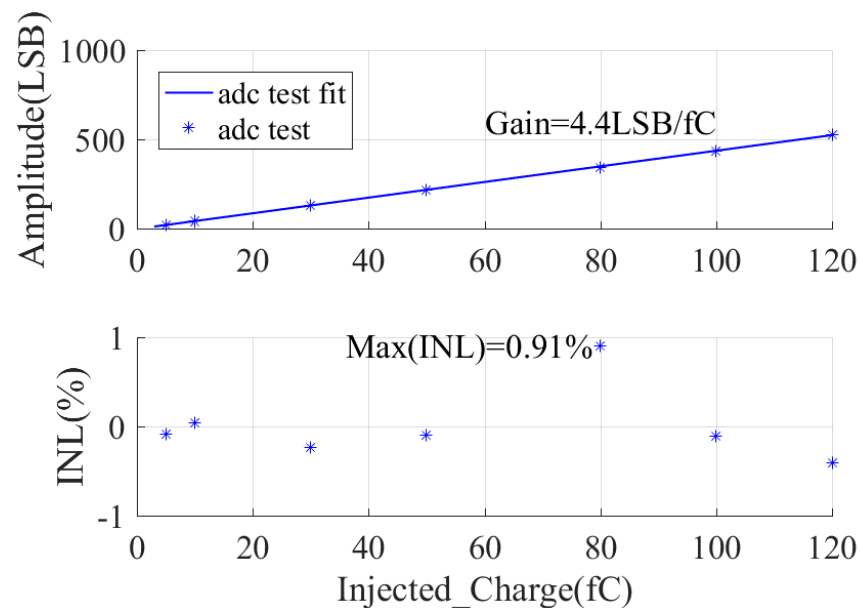


Non-Linearity

- Transient outputs



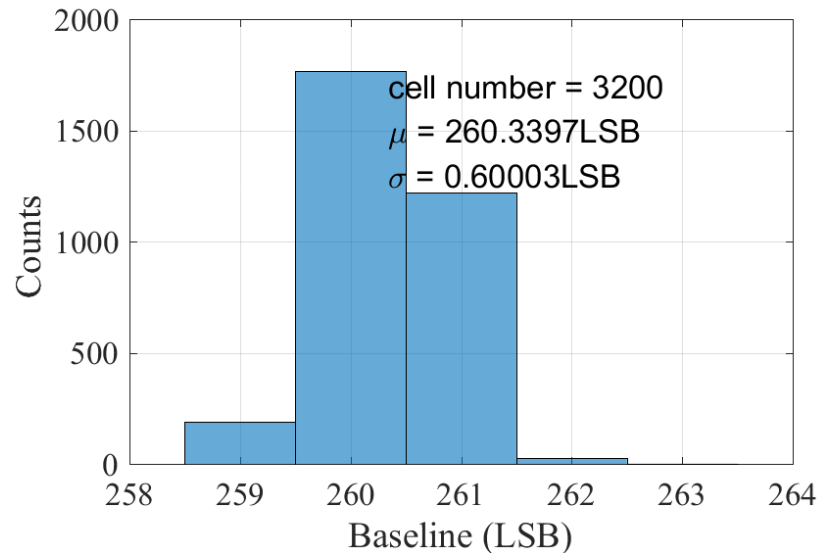
- The linearity @ gain = 10 mV/fC



$$\text{Gain} = 4.4 \text{ LSB/fC} = 4.4 \times 2.34 \text{ mV/fC} = 10.3 \text{ mV/fC}$$

Noise (Preliminary)

- The baseline fluctuation @ gain = 10 mV/fC
 - Parasitic PCB route capacitance not included
 - Significant contribution from ADC quantization noise

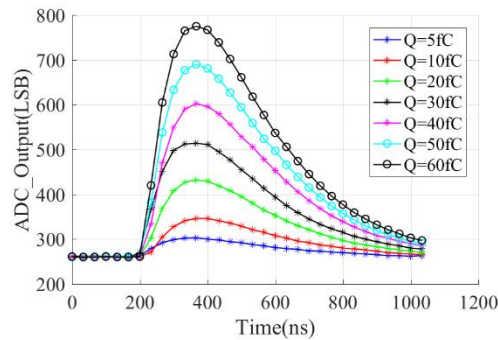


ENC = 852 e @ $C_{in} = 2$ pF, gain = 4.4 LSB/fC

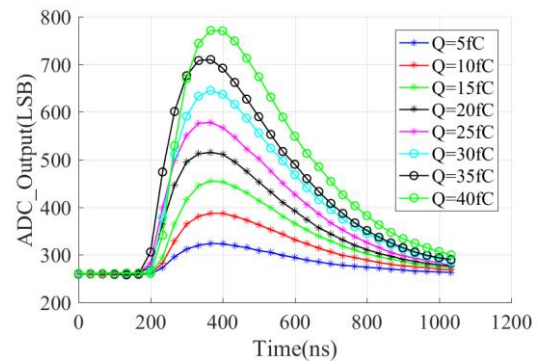
Non-Linearity @ 20-40 mV/fC

- Non-Linearity performance @ $C_{in} = 2 \text{ pF}$

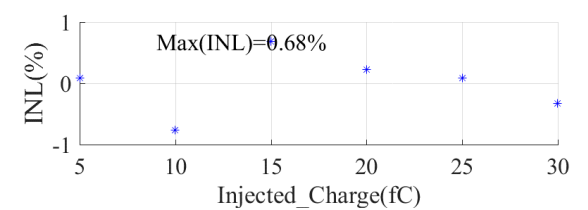
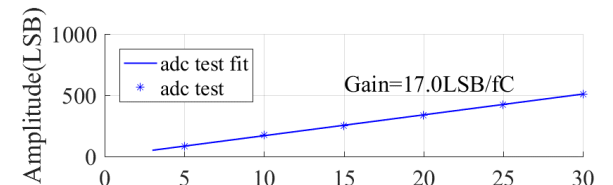
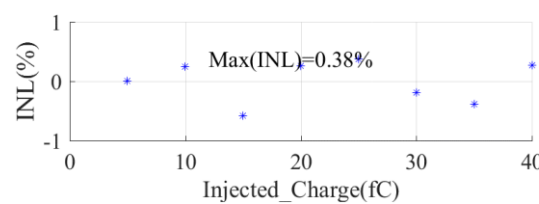
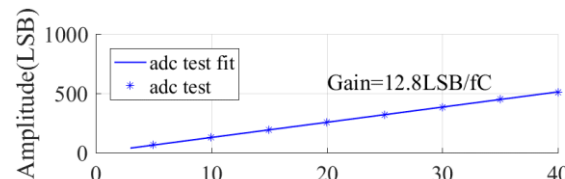
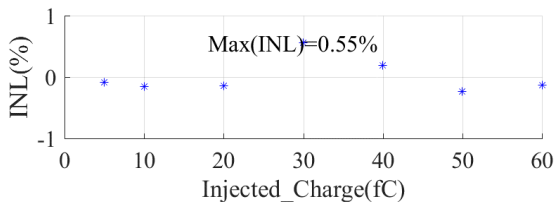
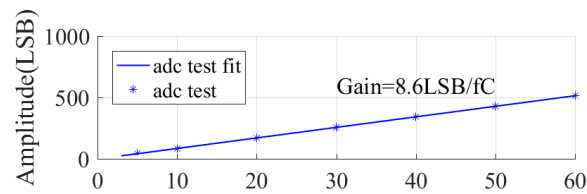
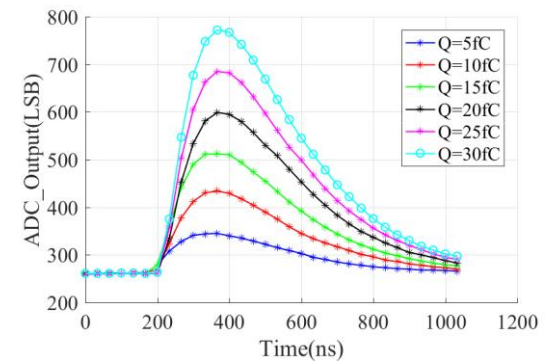
20 mV/fC



30 mV/fC



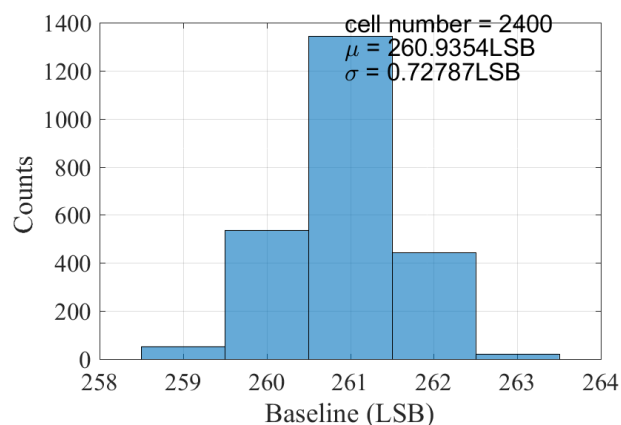
40 mV/fC



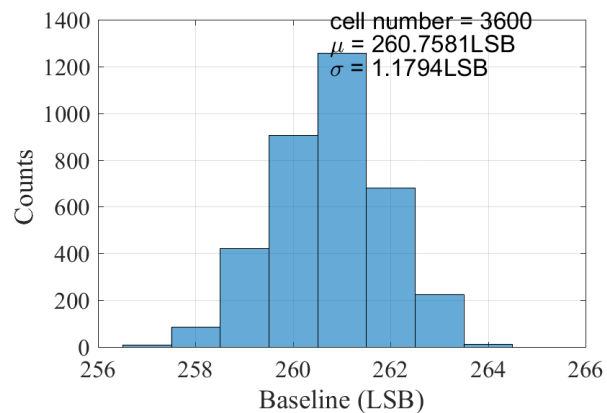
Noises @ 20-30 mV/fC (Preliminary)

- Noise performance @ $C_{in} = 2$ pF

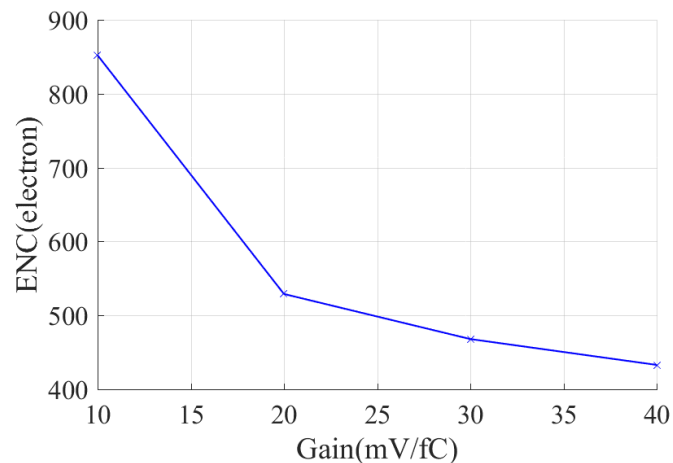
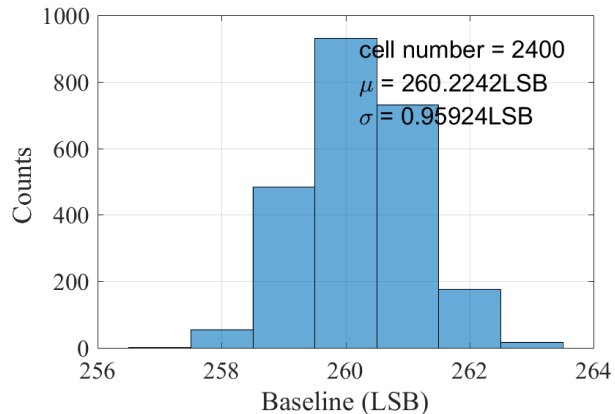
ENC = 529 e @ 20 mV/fC



ENC=433 e @ 40 mV/fC

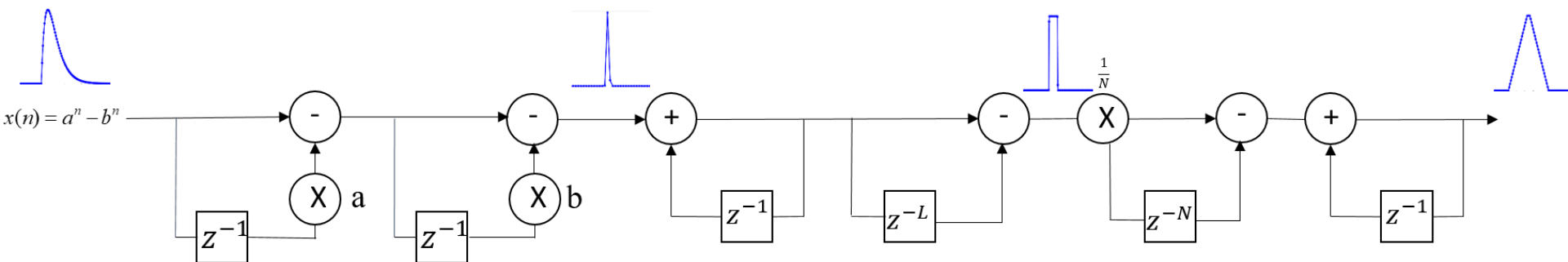


ENC=468 e @ 30 mV/fC



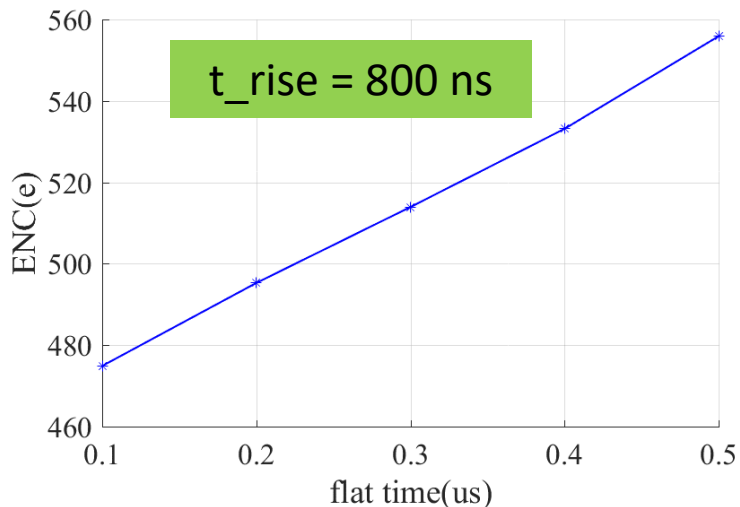
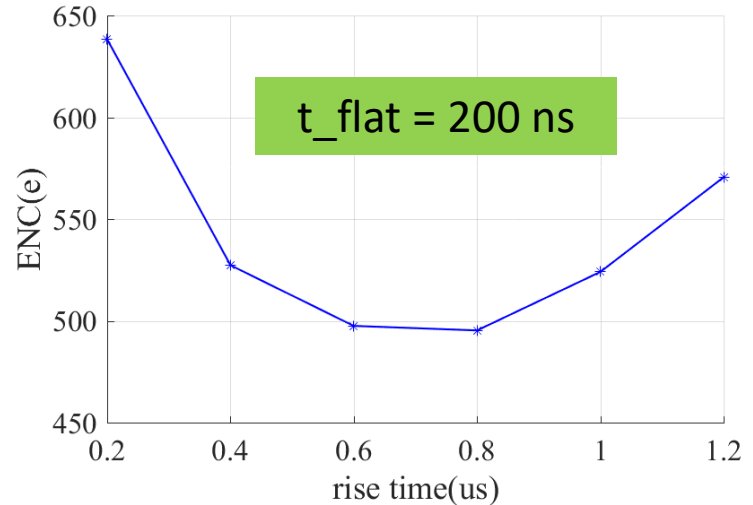
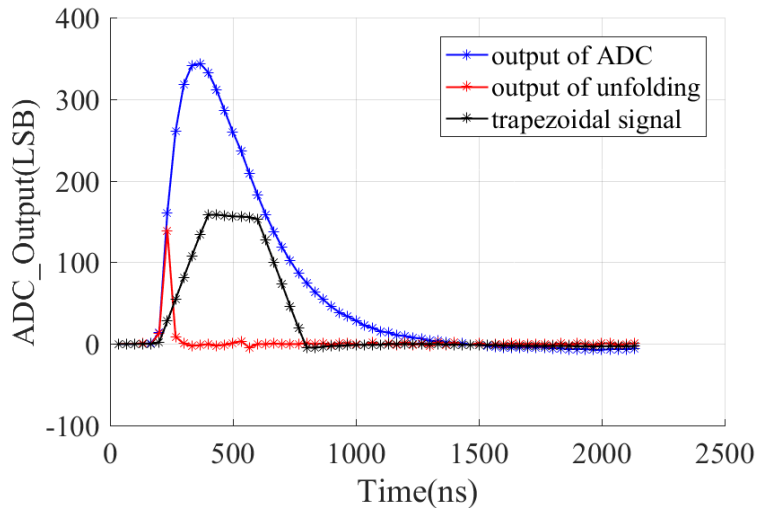
Digital Trapezoidal Filter (Preliminary)

- The waveform is symmetric , can achieve high SNR(signal to noise ratio)
- The ballistic deficit can be avoided
- Hardware resource is low cost, can be well implemented on chip
 - 2 multiplications ,6 additions and subtractions , some shift operations



Digital Trapezoidal Filter (Preliminary)

gain = 10 mV/fC



- More symmetric waveforms
- ENC noise
 - Original CR-RC ENC = 852 e
 - Min. ENC of 474 e after digital trapezoidal filter

Summary

- A 16 channel low power readout ASIC for TPC readout have been developed
 - The power consumption is **2.33 mW/channel**:
 - $P_{AFE}=1.43$ mW/channel
 - $P_{ADC} = 0.9$ mW/channel @ 40MS/s
 - ENC = **852 e** @ $C_{in}=2$ pF, gain=10 mV/fC and can be reduced to **474 e** using digital trapezoidal filter
- Future Plan
 - More ASIC evaluations: higher sampling rate, more detailed noise test, test with detectors...
 - Low power digital filter and data compression in FPGA/ASIC

Thank You